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Diodes Incorporated RS1D-13

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Datasheet of RS1D-13 - DIODE GEN PURP 200V 1A SMA

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RS1A/B - RS1M/B

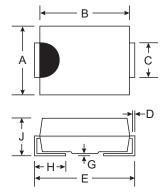
1.0A SURFACE MOUNT FAST RECOVERY RECTIFIER

Features

- Glass Passivated Die Construction
- Fast Recovery Time For High Efficiency
- Low Forward Voltage Drop and High Current Capability
- Surge Overload Rating to 30A Peak
- Ideally Suited for Automated Assembly
- Available in Lead Free Finish/RoHS Compliant Version (Note 4)

Mechanical Data

- Case: SMA/SMB
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solder Plated Terminal Solderable per MIL-STD-202, Method 208
- Also Available in Lead Free Plating (Matte Tin Finish).
 Please see Ordering Information, Note 6, on Page 1
- Polarity: Cathode Band or Cathode Notch
- SMA Weight: 0.064 grams (approximate)
- SMB Weight: 0.093 grams (approximate)



Dim	SI	/IΑ	SMB			
	Min	Max	Min	Max		
Α	2.29	2.92	3.30	3.94		
В	4.00	4.60	4.06	4.57		
С	1.27	1.63	1.96	2.21		
D	0.15	0.31	0.15	0.31		
E	4.80	5.59	5.00	5.59		
G	0.10	0.20	0.10	0.20		
Н	0.76	1.52	0.76	1.52		
J	2.01	2.30	2.00	2.40		

A, B, D, G, J, K, M Suffix Designates SMA Package AB, BB, DB, GB, JB, KB, MB Suffix Designates SMB Package

Maximum Ratings and Electrical Characteristics @ TA = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	RS1 A/AB	RS1 B/BB	RS1 D/DB	RS1 G/GB	RS1 J/JB	RS1 K/KB	RS1 M/MB	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	V _{R(RMS)}	35	70	140	280	420	560	700	V
Average Rectified Output Current @ T _T = 120°C	lo				1.0			•	Α
Non-Repetitive Peak Forward Surge Current, 8.3ms single half sine-wave Superimposed on Rated Load (JEDEC Method)		30					А		
Forward Voltage Drop @ I _F = 1.0A	V _{FM}	1.3				V			
	I _{RM}	5.0 200			μА				
Reverse Recovery Time (Note 3)		150 250 500			00	ns			
Typical Total Capacitance (Note 2)		15					pF		
Typical Thermal Resistance, Junction to Terminal (Note 1)		20						°C/W	
Operating and Storage Temperature Range		-65 to +150						°C	

Notes: 1. Valid provided that terminals are kept at ambient temperature.

- 2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.
- 3. Reverse Recovery Test Conditions: $I_F = 0.5A$, $I_R = 1.0A$, $I_{rr} = 0.25A$. See figure 5.
- 4. RoHS revision 13.2.2003. Glass and High Temperature Solder Exemptions Applied, see EU Directive Annex Notes 5 and 7.

Ordering Information (Note 5 & 6)

Device*	Packaging	Shipping
RS1x-13	SMA	5000/Tape & Reel
RS1xB-13	SMB	3000/Tape & Reel

^{*} x = Device type, e.g. RS1D-13 (SMA package); RS1JB-13 (SMB package).

lotes: 5. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

6. For Lead Free Finish/RoHS Compliant version part numbers, please add "-F" suffix to the part numbers above. Example: RS1B-13-F.

1.2 10 I_E INSTANTANEOUS FORWARD CURRENT (A) Io, AVERAGE RECTIFIED CURRENT (A) 1.0 1.0 0.8 0.6 0.1 0.4 0.2 T_i = 25°C I_F Pulse Width: 300μs 0.01 0 0.4 0 8.0 25 50 75 100 125 150 175 1.6 T_T, TERMINAL TEMPERATURE (°C) V_F, INSTANTANEOUS FORWARD VOLTAGE (V) Fig. 1 Forward Current Derating Curve Fig. 2 Typical Forward Characteristics 30 I_{FSM}, PEAK FORWARD SURGE CURRENT (A) IR, INSTANTANEOUS REVERSE CURRENT (µA) 1000 Single Half-Sine-Wave (JEDEC Method) T_i = 125°C T_i = 150°C 100 20 10 10 $T_i = 25^{\circ}C$ 1.0 0.1 0 20 0 40 60 80 100 120 140 100 NUMBER OF CYCLES AT 60Hz PERCENT OF RATED PEAK REVERSE VOLTAGE (%) Fig. 3 Forward Surge Current Derating Curve Fig. 4 Typical Reverse Characteristics +0.5A 50Ω NI (Non-inductive) 10Ω NI Device Under (-) 0A Test 50V DC Pulse -0.25A Generator Approx (Note 2) (-) 1.0Ω Oscilloscope (Note 1) (+) (O) NI -1.0A Notes: 1. Rise Time = 7.0ns max. Input Impedance = $1.0M\Omega$, 22pF. Set time base for 50/100 ns/cm 2. Rise Time = 10ns max. Input Impedance = 50Ω .

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Fig. 5 Reverse Recovery Time Characteristic and Test Circuit